



**THE DATASHEET OF
AOT8N80L**



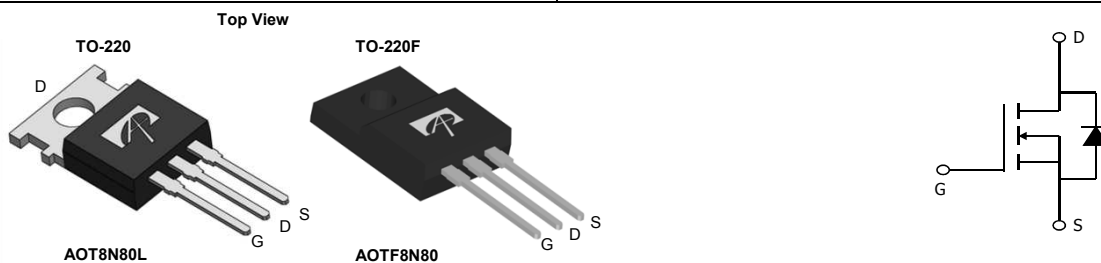
General Description

The AOT8N80L & AOTF8N80 have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

Product Summary

| | |
|---------------------------------|------------|
| V_{DS} | 900V@150°C |
| I_D (at $V_{GS}=10V$) | 7.4A |
| $R_{DS(on)}$ (at $V_{GS}=10V$) | < 1.63Ω |

100% UIS Tested
 100% R_g Tested


Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

| Parameter | Symbol | AOT8N80L | AOTF8N80 | Units |
|--|----------------|-------------------|----------|-------|
| Drain-Source Voltage | V_{DS} | 800 | | V |
| Gate-Source Voltage | V_{GS} | ±30 | | V |
| Continuous Drain Current | I_D | $T_C=25^\circ C$ | 7.4 | 7.4* |
| | | $T_C=100^\circ C$ | 4.6 | 4.6* |
| Pulsed Drain Current ^C | I_{DM} | 26 | | A |
| Avalanche Current ^C | I_{AR} | 3.8 | | A |
| Repetitive avalanche energy ^C | E_{AR} | 217 | | mJ |
| Single pulsed avalanche energy ^G | E_{AS} | 433 | | mJ |
| Peak diode recovery dv/dt | dv/dt | 5 | | V/ns |
| Power Dissipation ^B | P_D | $T_C=25^\circ C$ | 245 | 50 |
| | | Derate above 25°C | 2.0 | 0.4 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | | °C |
| Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds | T_L | 300 | | °C |

Thermal Characteristics

| Parameter | Symbol | AOT8N80L | AOTF8N80 | Units |
|--|-----------------|----------|----------|-------|
| Maximum Junction-to-Ambient ^{A,D} | $R_{\theta JA}$ | 65 | 65 | °C/W |
| Maximum Case-to-sink ^A | $R_{\theta CS}$ | 0.5 | -- | °C/W |
| Maximum Junction-to-Case | $R_{\theta JC}$ | 0.51 | 2.5 | °C/W |

* Drain current limited by maximum junction temperature.

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units | |
|------------------------------------|---|---|------|------|------|-------|----|
| STATIC PARAMETERS | | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0V, T _J =25°C | 800 | | | V | |
| | | I _D =250μA, V _{GS} =0V, T _J =150°C | | 900 | | | |
| BV _{DSS} /ΔT _J | Breakdown Voltage Temperature Coefficient | I _D =250μA, V _{GS} =0V | | 0.86 | | V/°C | |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =800V, V _{GS} =0V | | | 1 | μA | |
| | | V _{DS} =640V, T _J =125°C | | | 10 | | |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} =±30V | | | ±100 | nA | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =5V, I _D =250μA | 3.3 | 3.9 | 4.5 | V | |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} =10V, I _D =4A | | 1.35 | 1.63 | Ω | |
| g _{FS} | Forward Transconductance | V _{DS} =40V, I _D =4A | | 9 | | S | |
| V _{SD} | Diode Forward Voltage | I _S =1A, V _{GS} =0V | | 0.72 | 1 | V | |
| I _S | Maximum Body-Diode Continuous Current | | | | 7.4 | A | |
| I _{SM} | Maximum Body-Diode Pulsed Current | | | | 26 | A | |
| DYNAMIC PARAMETERS | | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =25V, f=1MHz | 1100 | 1375 | 1650 | pF | |
| C _{oss} | Output Capacitance | | 70 | 101 | 132 | pF | |
| C _{rss} | Reverse Transfer Capacitance | | 6 | 11 | 16 | pF | |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, f=1MHz | 1.7 | 3.5 | 5.3 | Ω | |
| SWITCHING PARAMETERS | | | | | | | |
| Q _g | Total Gate Charge | V _{GS} =10V, V _{DS} =640V, I _D =8A | 20 | 26 | 32 | nC | |
| Q _{gs} | Gate Source Charge | | | | 7.3 | | nC |
| Q _{gd} | Gate Drain Charge | | | | 9.1 | | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =10V, V _{DS} =400V, I _D =8A, R _G =25Ω | | | 35 | ns | |
| t _r | Turn-On Rise Time | | | | 51 | ns | |
| t _{D(off)} | Turn-Off DelayTime | | | | 69 | ns | |
| t _f | Turn-Off Fall Time | | | | 41 | ns | |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =8A, di/dt=100A/μs, V _{DS} =100V | 380 | 484 | 585 | ns | |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =8A, di/dt=100A/μs, V _{DS} =100V | 4.5 | 6 | 7.5 | μC | |

- A. The value of R_{θJA} is measured with the device in a still air environment with T_A=25° C.
 B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
 C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C, Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.
 D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
 E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.
 F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
 G. L=60mH, I_{AS}=3.8A, V_{DD}=150V, R_G=25Ω, Starting T_J=25° C

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

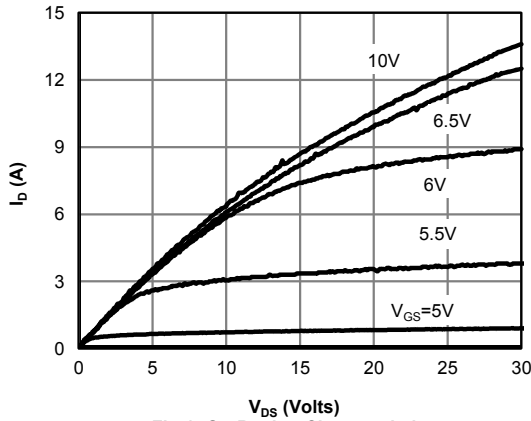


Fig 1: On-Region Characteristics

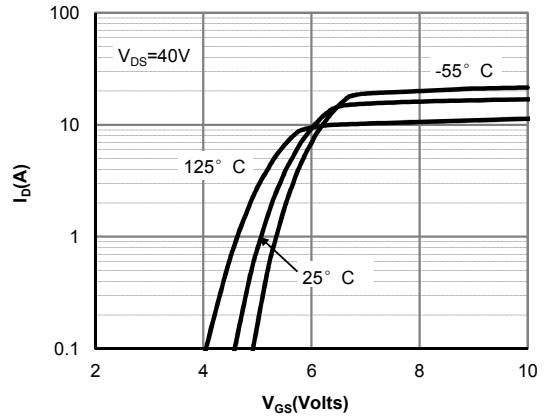


Figure 2: Transfer Characteristics

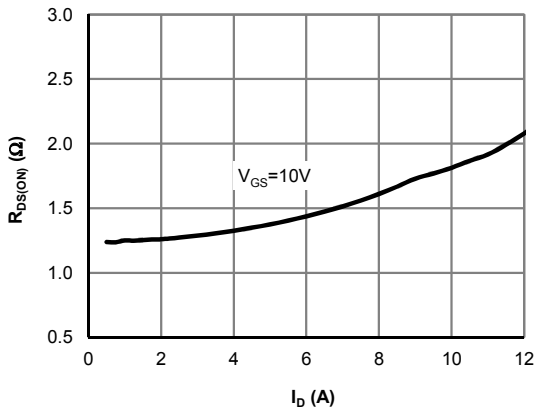


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

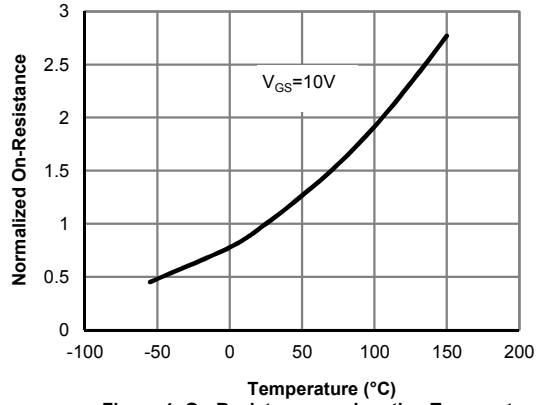


Figure 4: On-Resistance vs. Junction Temperature

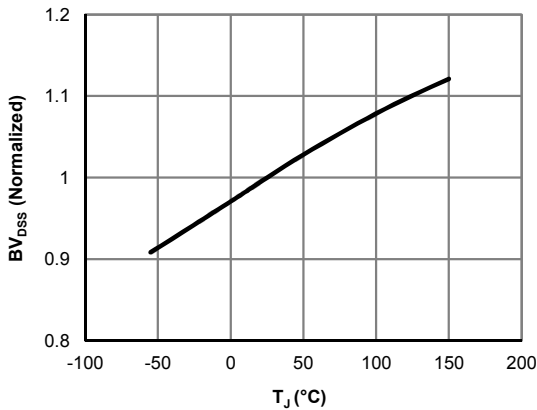


Figure 5: Break Down vs. Junction Temperature

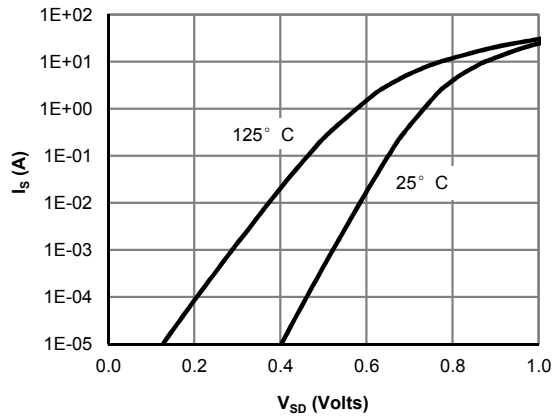


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

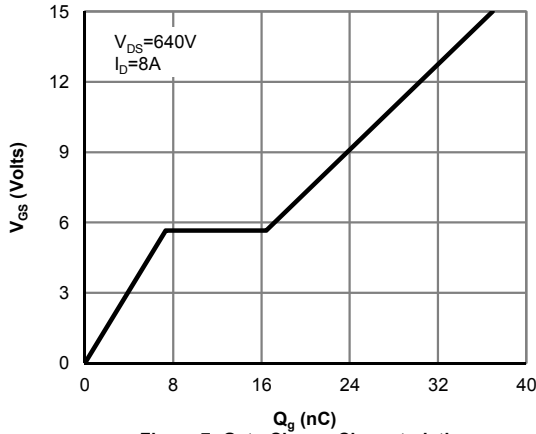


Figure 7: Gate-Charge Characteristics

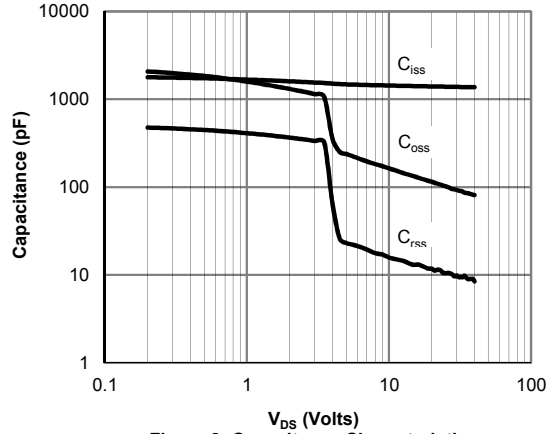


Figure 8: Capacitance Characteristics

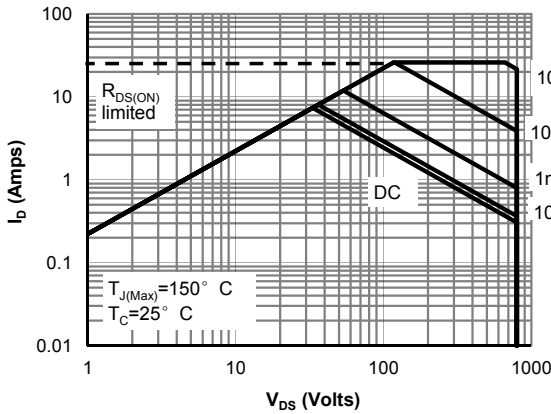


Figure 9: Maximum Forward Biased Safe Operating Area for AOT8N80L (Note F)

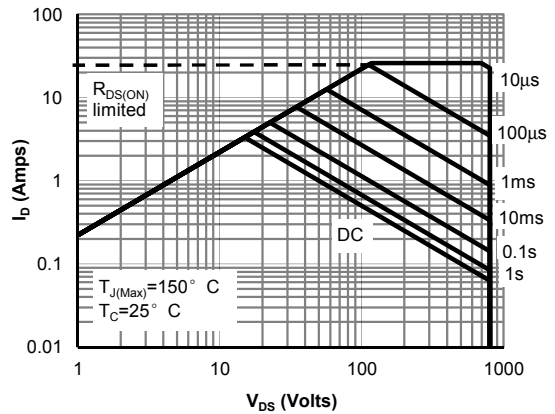


Figure 10: Maximum Forward Biased Safe Operating Area for AOTF8N80 (Note F)

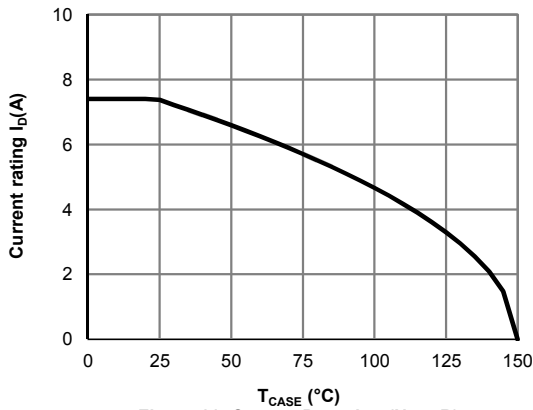


Figure 11: Current De-rating (Note B)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

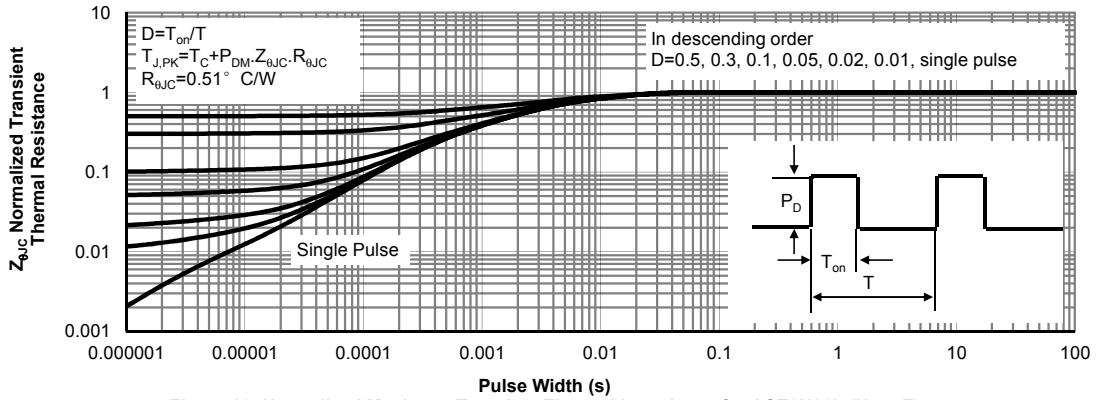


Figure 12: Normalized Maximum Transient Thermal Impedance for AOT8N80L (Note F)

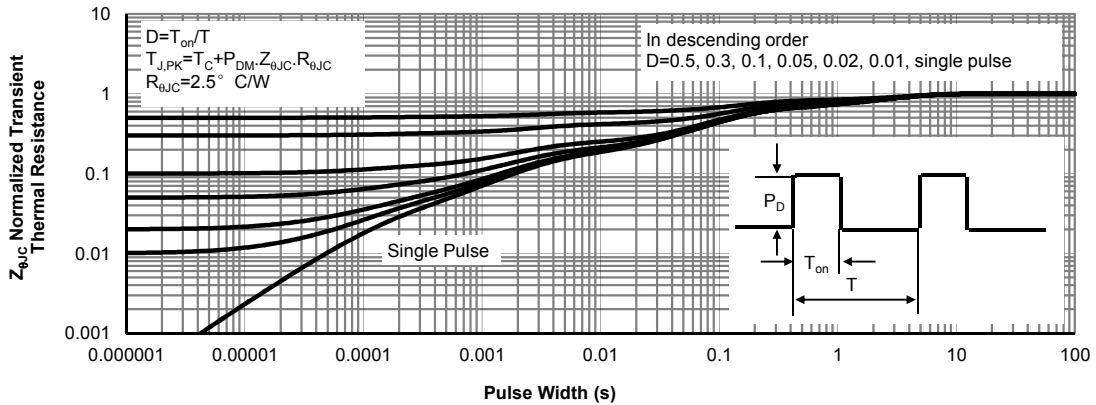
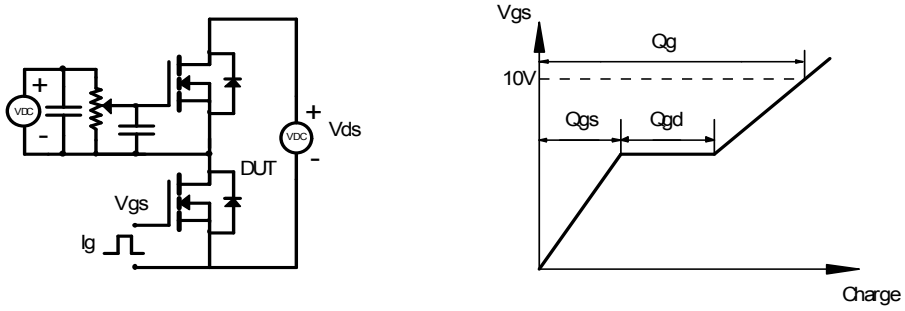
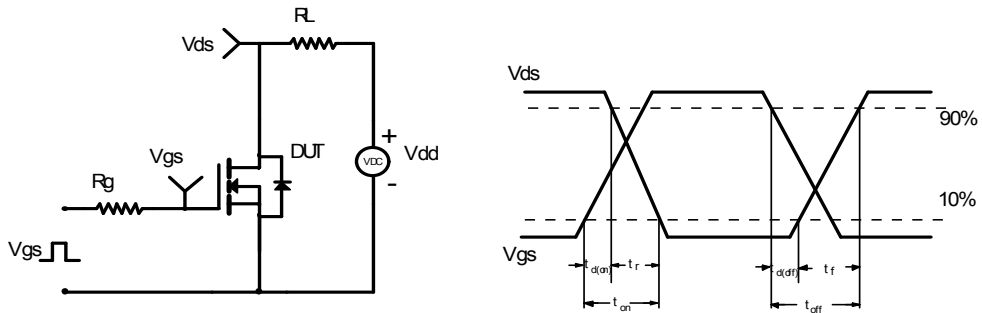


Figure 13: Normalized Maximum Transient Thermal Impedance for AOTF8N80 (Note F)

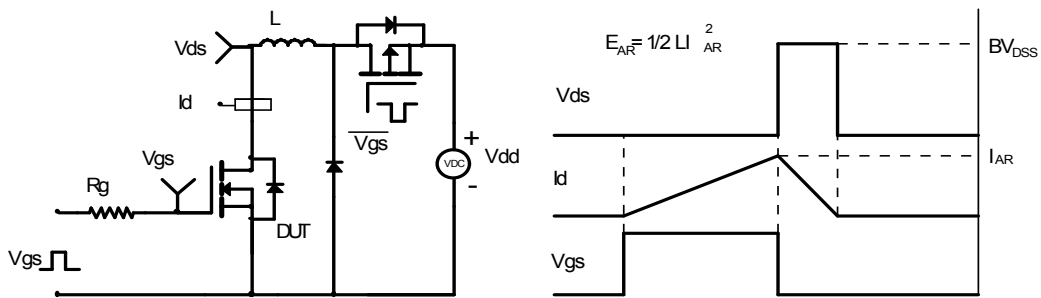
Gate Charge Test Circuit & Waveform



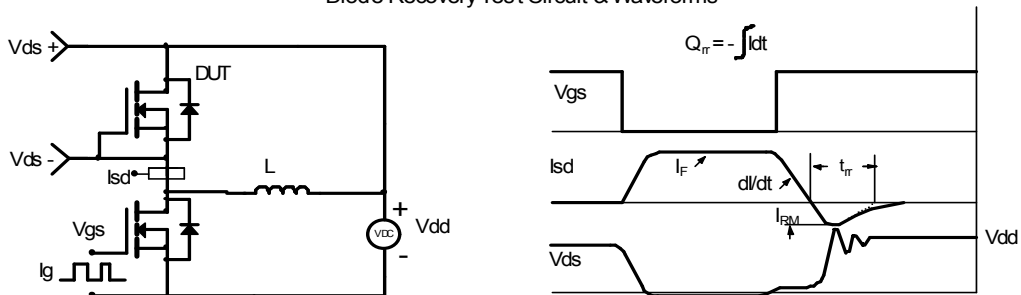
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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